

CMKT5089M10

SURFACE MOUNT
DUAL NPN SILICON
MATCHED h_{FE} TRANSISTORS

ULTRAmulti™



SOT-363 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKT5089M10 consists of two (2) individually isolated 5089 NPN silicon transistors with matched h_{FE} . This ULTRAmulti™ device is manufactured by the epitaxial planar process and epoxy molded in an SOT-363 surface mount package. The CMKT5089M10 has been designed for applications requiring high gain and low noise.

MARKING CODE: C9M0

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CBO} 30
 V_{CEO} 25
 V_{EBO} 4.5
 I_C 50
 P_D 350
 T_J, T_{stg} -65 to +150
 θ_{JA} 357

UNITS

V
V
V
mA
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=15\text{V}$		50	nA
I_{EBO}	$V_{EB}=4.5\text{V}$		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	30		V
BV_{CEO}	$I_C=1.0\text{mA}$	25		V
BV_{EBO}	$I_E=100\mu\text{A}$	4.5		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.5	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.8	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=0.1\text{mA}$	400	1200	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	450		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	400		
f_T	$V_{CE}=5.0\text{V}, I_C=500\mu\text{A}, f=20\text{MHz}$	50		MHz
C_{ob}	$V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$		4.0	pF
C_{ib}	$V_{BE}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		10	pF
h_{fe}	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	450	1800	
NF	$V_{CE}=5.0\text{V}, I_C=100\mu\text{A}, R_S=1.0\text{k}\Omega,$ $f=10\text{Hz to } 15.7\text{kHz}$		2.0	dB

MATCHING CHARACTERISTICS:

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE1}/h_{FE2}^*	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	0.9	1.0	
$ V_{BE1}-V_{BE2} $	$V_{CE}=5.0\text{V}, I_C=100\mu\text{A}$		5.0	mV

* The lowest h_{FE} reading is taken as h_{FE1} .

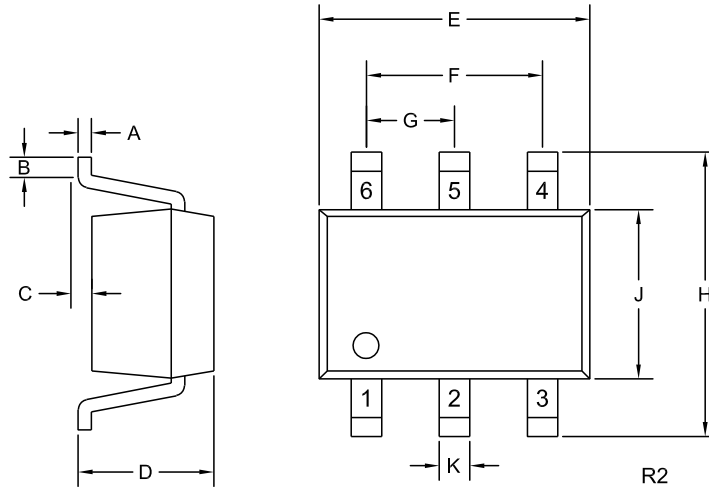
R4 (13-January 2010)

CMKT5089M10

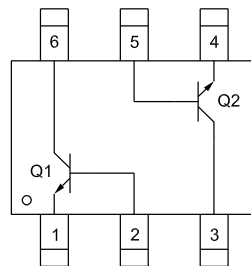
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SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

MARKING CODE: C9M0

DIMENSIONS

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)

R4 (13-January 2010)